



# The Search for True Chemicurrent from Catalytic Nanodiodes

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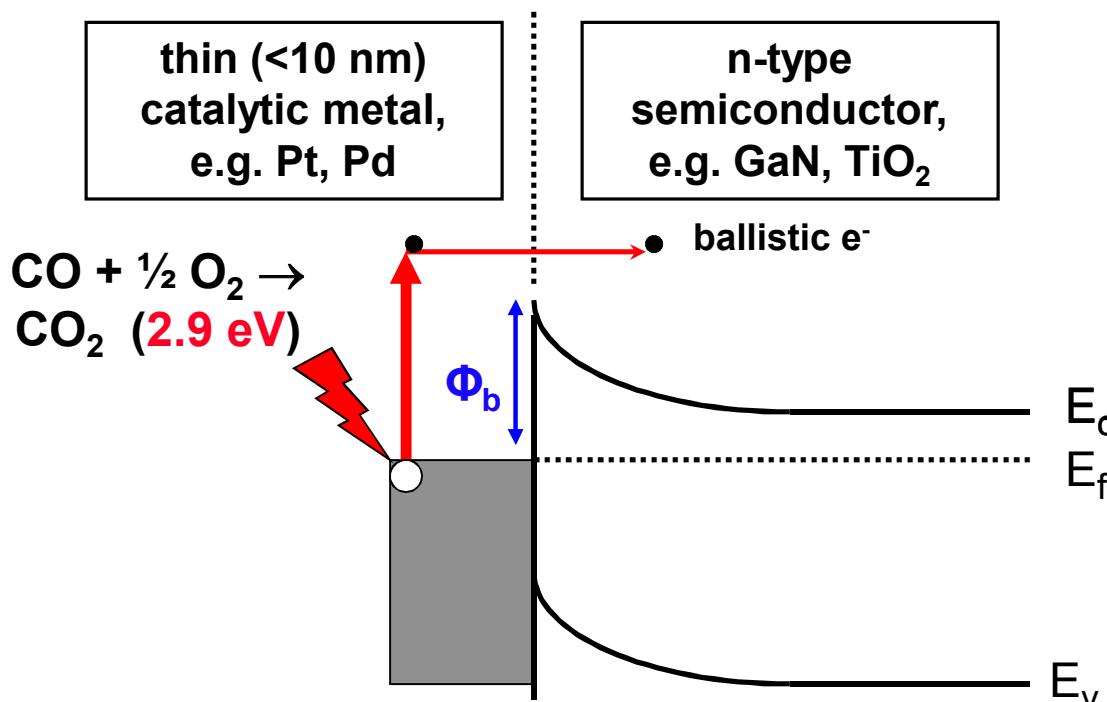
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GaN deposition – Dan Koleske

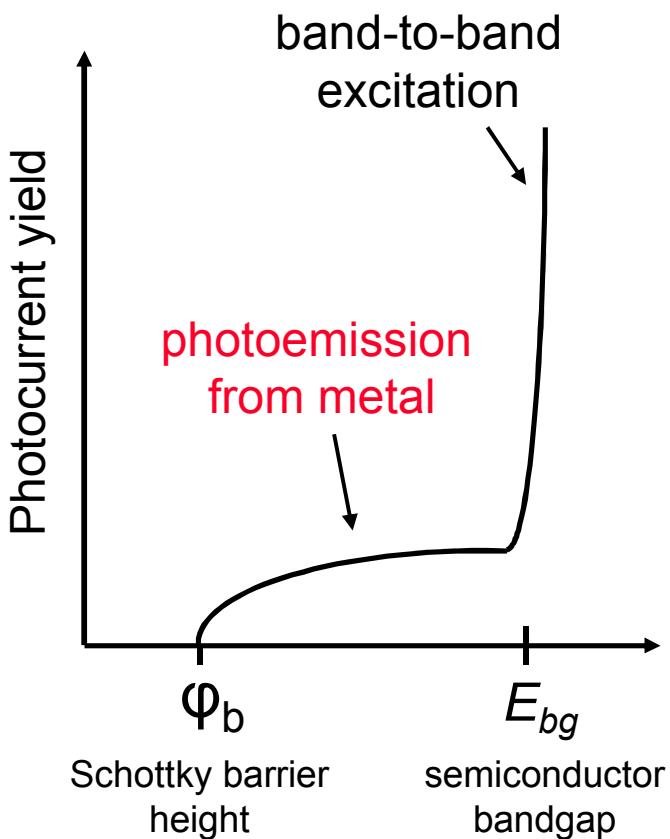
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# What is a “Catalytic Nanodiode”?

- The catalytic nanodiode is a simple Schottky diode that converts chemical energy directly into electrical energy, via electronic excitation, i.e. hot electrons
- Somorjai et al. reported (2005) a reaction quantum yield (electrons/CO<sub>2</sub>) up to ~75% for the CO oxidation reaction on Pt/TiO<sub>2</sub>, coined the term “catalytic nanodiode”

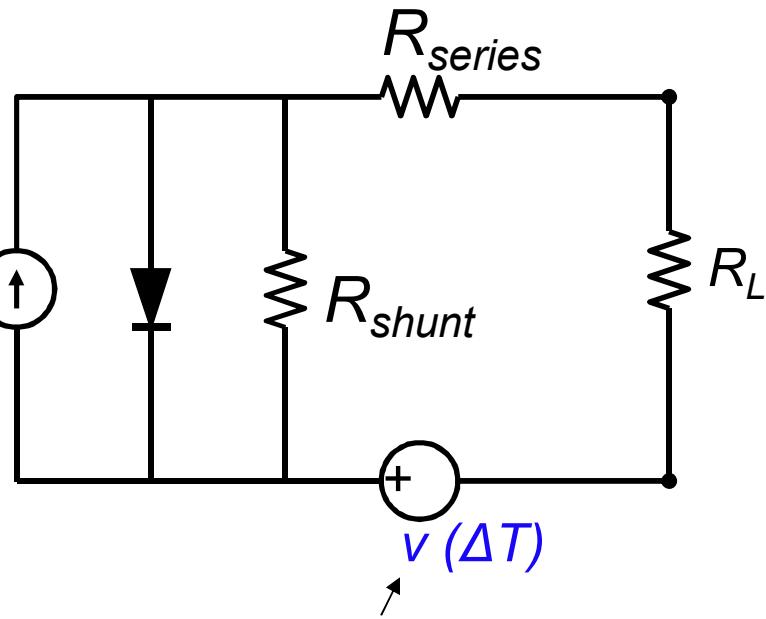


# Best analogy to catalytic nanodiode is a Schottky diode solar cell or photodiode with sub-bandgap illumination



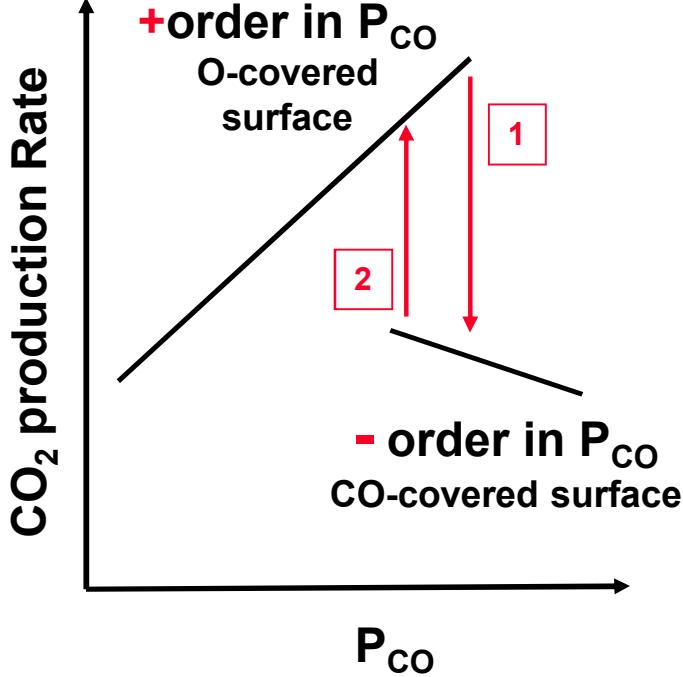
replace photocurrent with chemicurrent  $i$

equivalent circuit

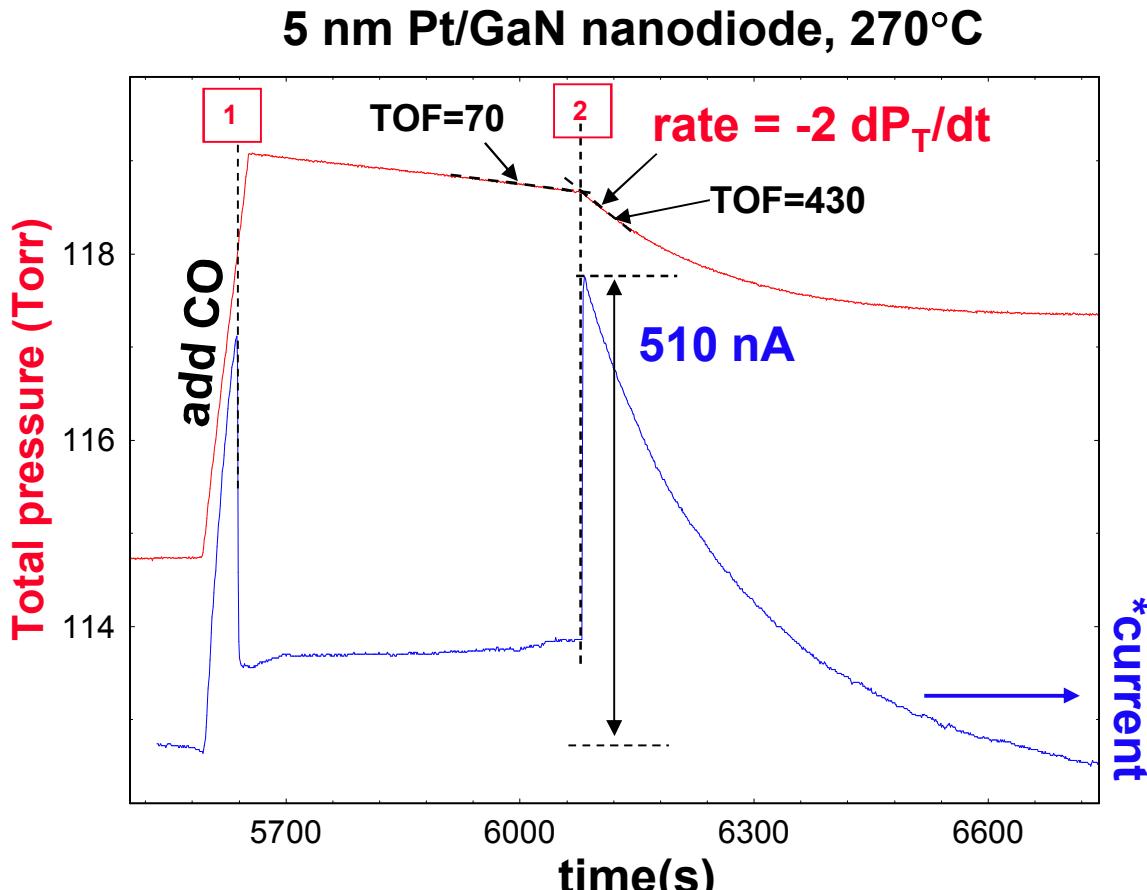


thermoelectric voltage,  
typically 0.3-1.0 mV  
before reaction conditions

# Kinetic phase transition during CO oxidation on Pt is observable using the nanodiode current



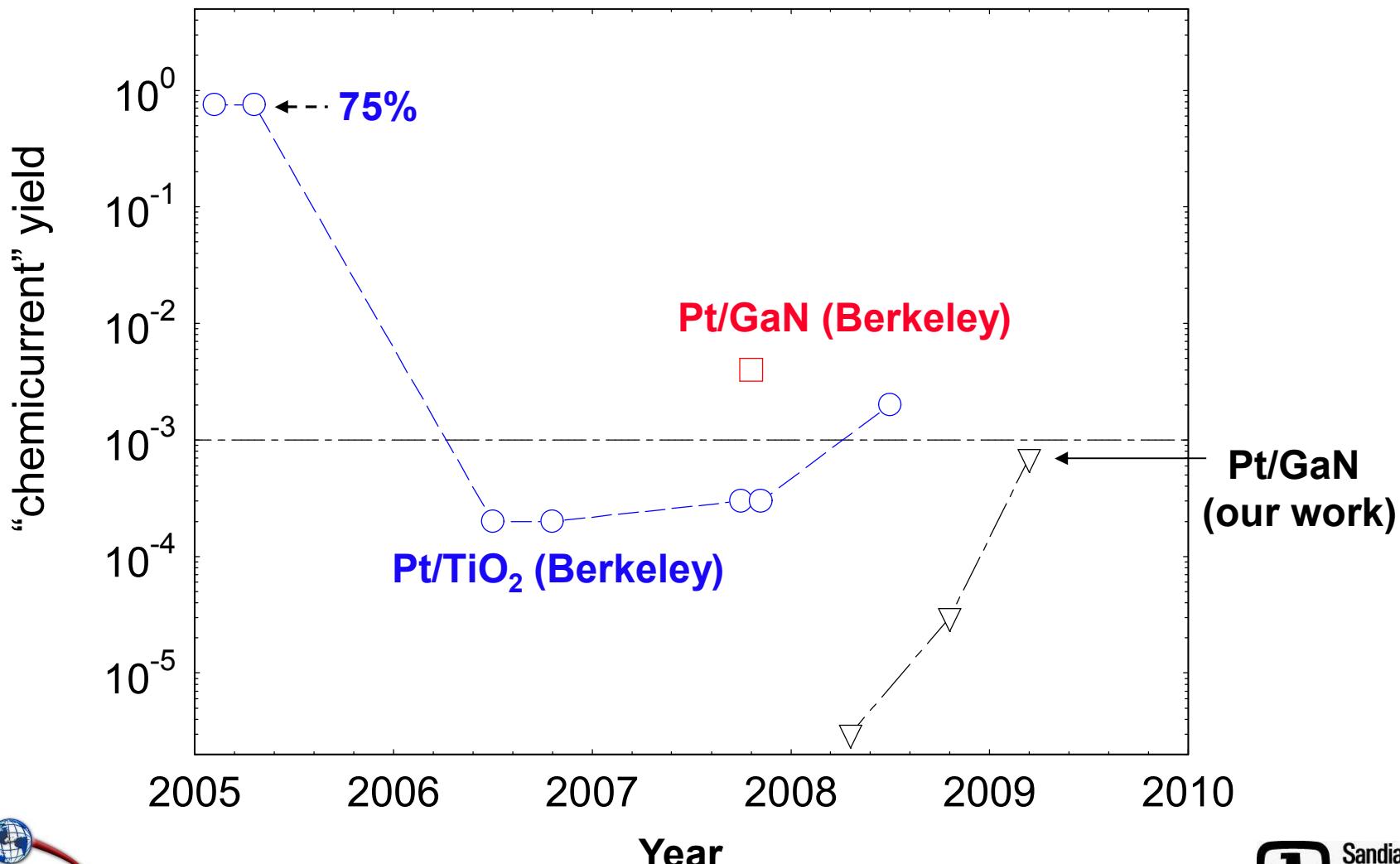
ref: e.g. Creighton JPC 1981



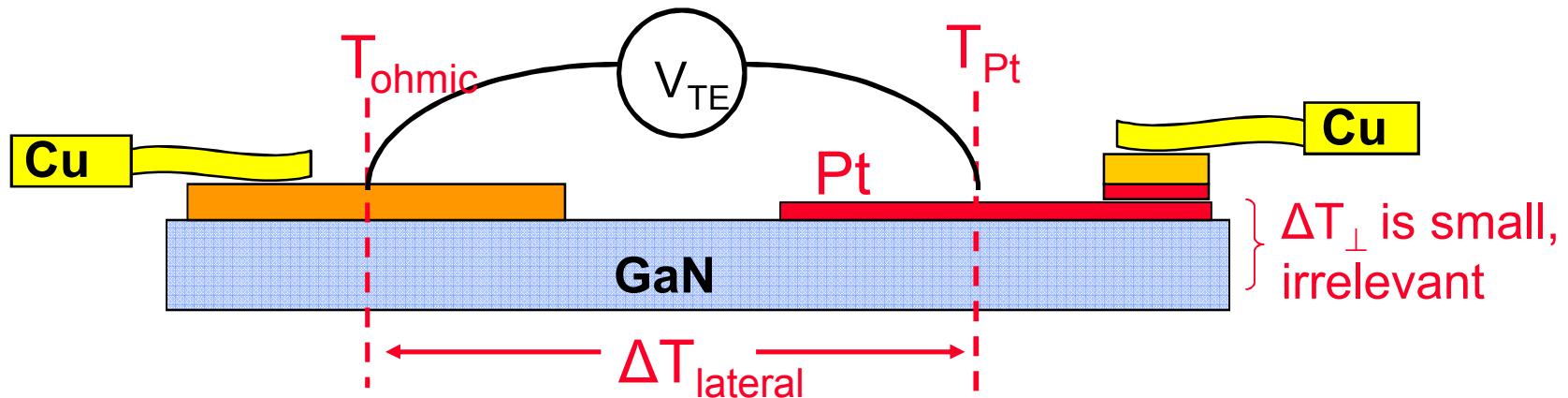
we use this lineshape as a fingerprint

\* using solar cell convention for chemicurrent

Our yield measurements are in reasonable agreement with more recent Somorjai results (post 2005)



# Is the electronic signal due to “chemicurrent” or is it derived from a voltage source?



$$V_{TE} \sim (S_{GaN} - S_{Cu})\Delta T_{lat} + \text{much smaller terms}$$

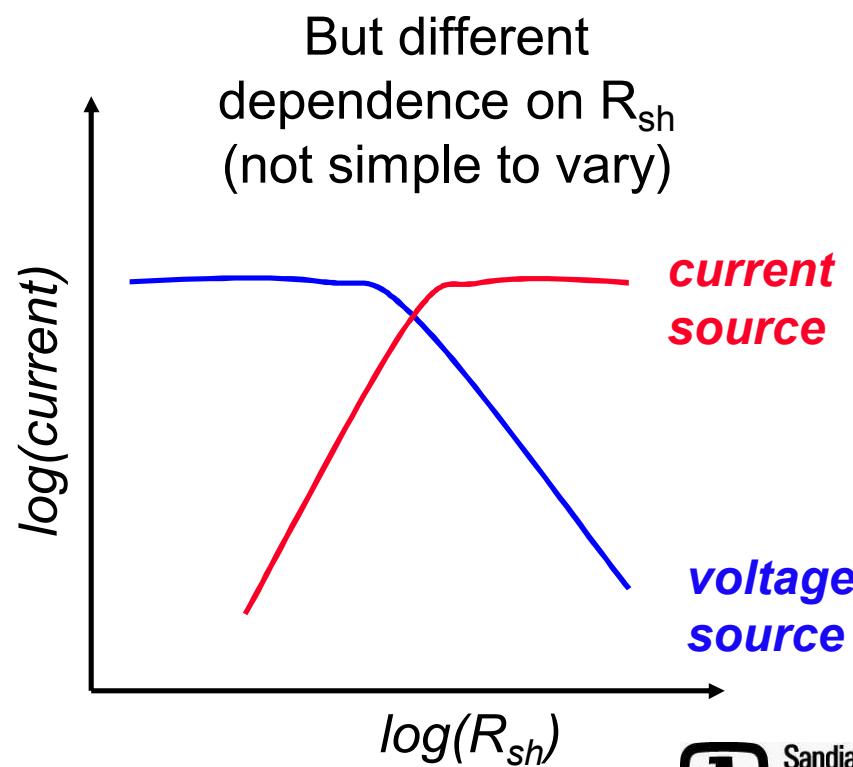
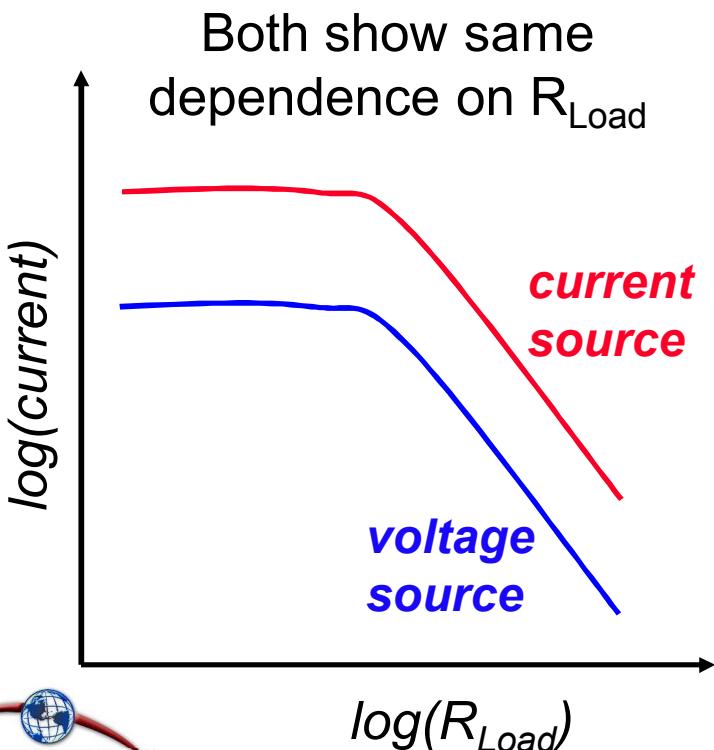
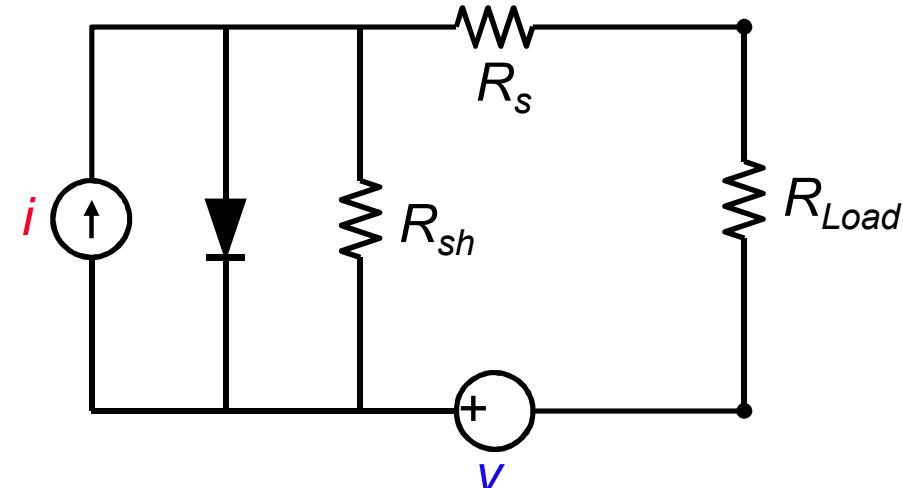
$V_{TE}$  is mostly determined by:

- 1) GaN Seebeck coefficient;  $S_{GaN}$  [ typically  $\sim -400 \mu\text{V/deg}$ ]
- 2) the lateral temperature difference,  $\Delta T_{lat}$

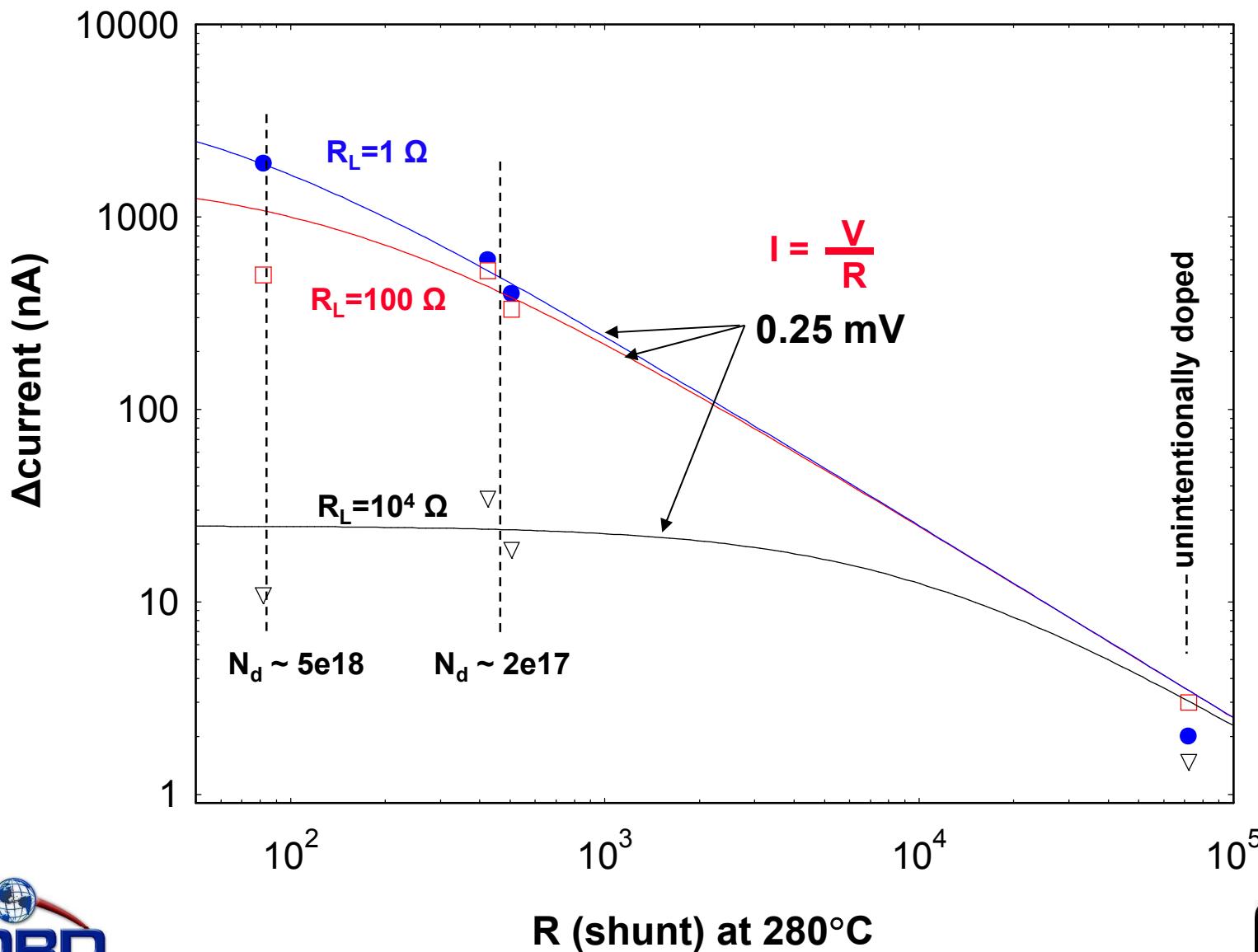
only need  $\Delta T_{lat} \sim 1^\circ\text{C}$



How can you differentiate a current source from a voltage source when shunt ( $R_{sh}$ ) and series ( $R_s$ ) resistance are present?



Vary  $R_{\text{shunt}}$  by varying GaN doping level,  
behavior is indicative of a voltage source





# The 2 Burning Questions

**What is the magnitude of the Pt temperature rise,  
 $\Delta T_{Pt}$ , during reaction?**

**How much is the lateral temperature gradient,  
 $\Delta T_{lat}$ , affected by the reaction?**

Reaction is exothermic; 68 kcal/mole,  $\sim 2.9\text{eV}/\text{CO}_2$

For reaction TOF = 400, power density is **300 mW/cm<sup>2</sup>**

For reference: heater is dissipating 700 mW/cm<sup>2</sup> at 270°C

The heat liberated only needs to increase  **$\Delta T_{lat}$**  by  $\sim 1^\circ\text{C}$  in order to generate the measured signals



## We use both theoretical and experimental methods to address these 2 questions

Theoretical:

- “Simple” 1D and quasi-2D calculations

- Full 3D simulations of entire reactor

Experimental:

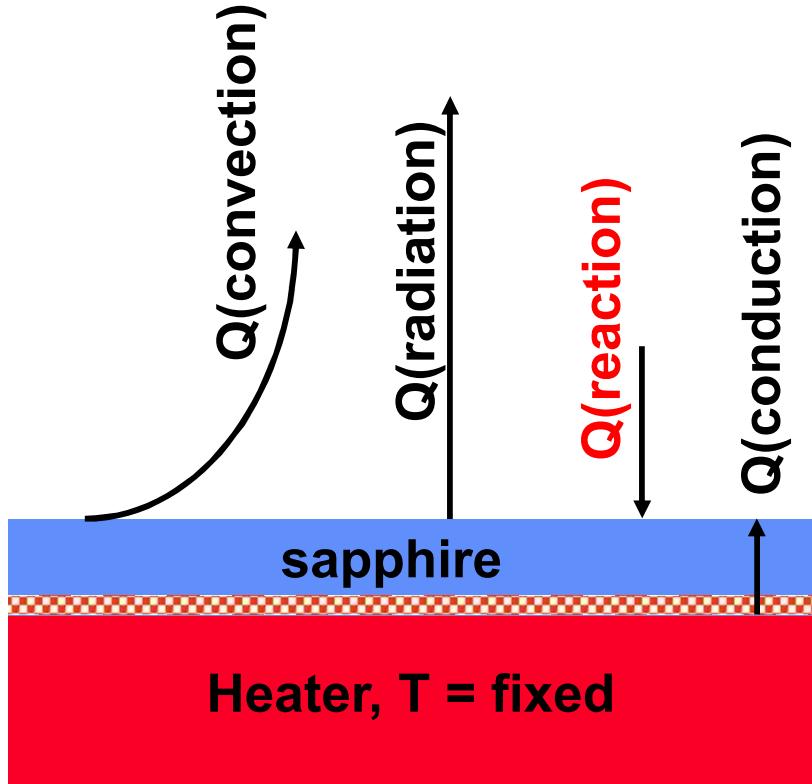
- mid-IR optical pyrometry of Pt surface:  $\Delta T_{Pt}$

- Thermocouple measurements of electrical contacts:  $\Delta T_{lat}$

# 1D calculation with isothermal heater

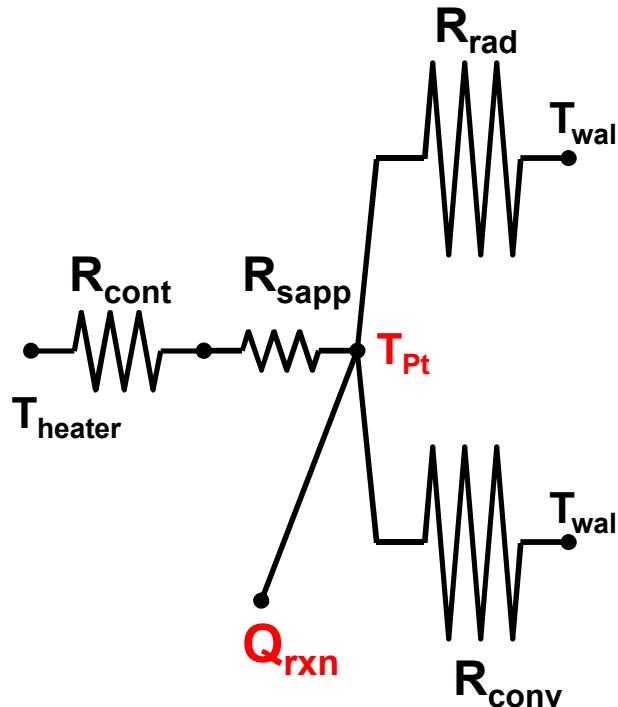
## Physical model

chamber wall,  $T = \text{fixed}$

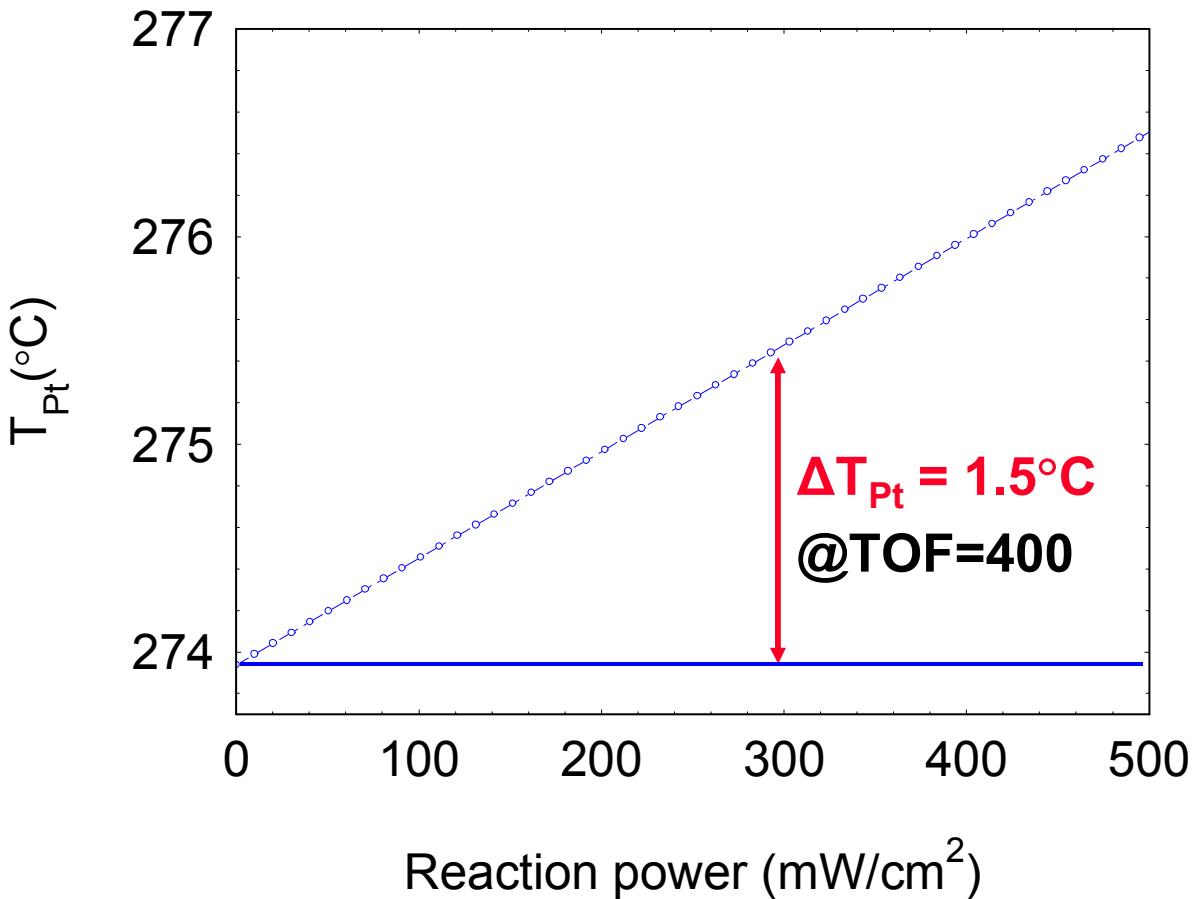


## Equivalent thermal circuit

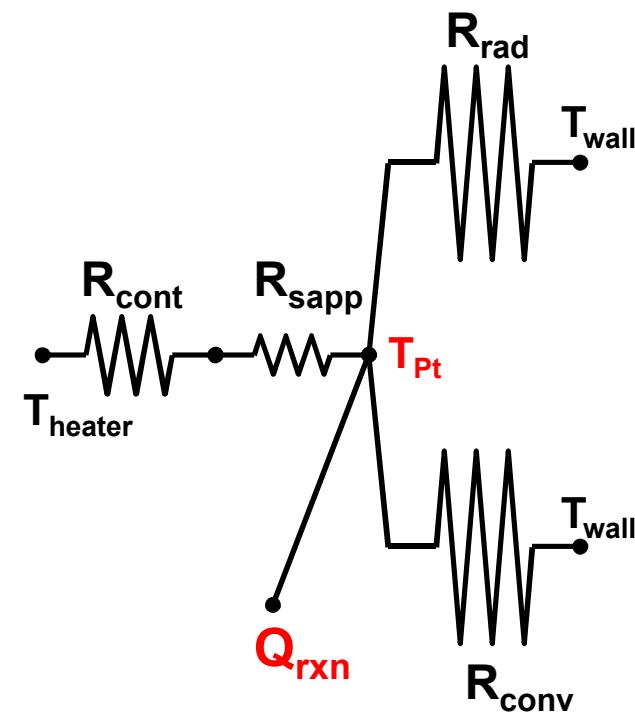
$$\Delta T = Q \cdot R_{\text{thermal}}$$



# 1D calculation with isothermal heater

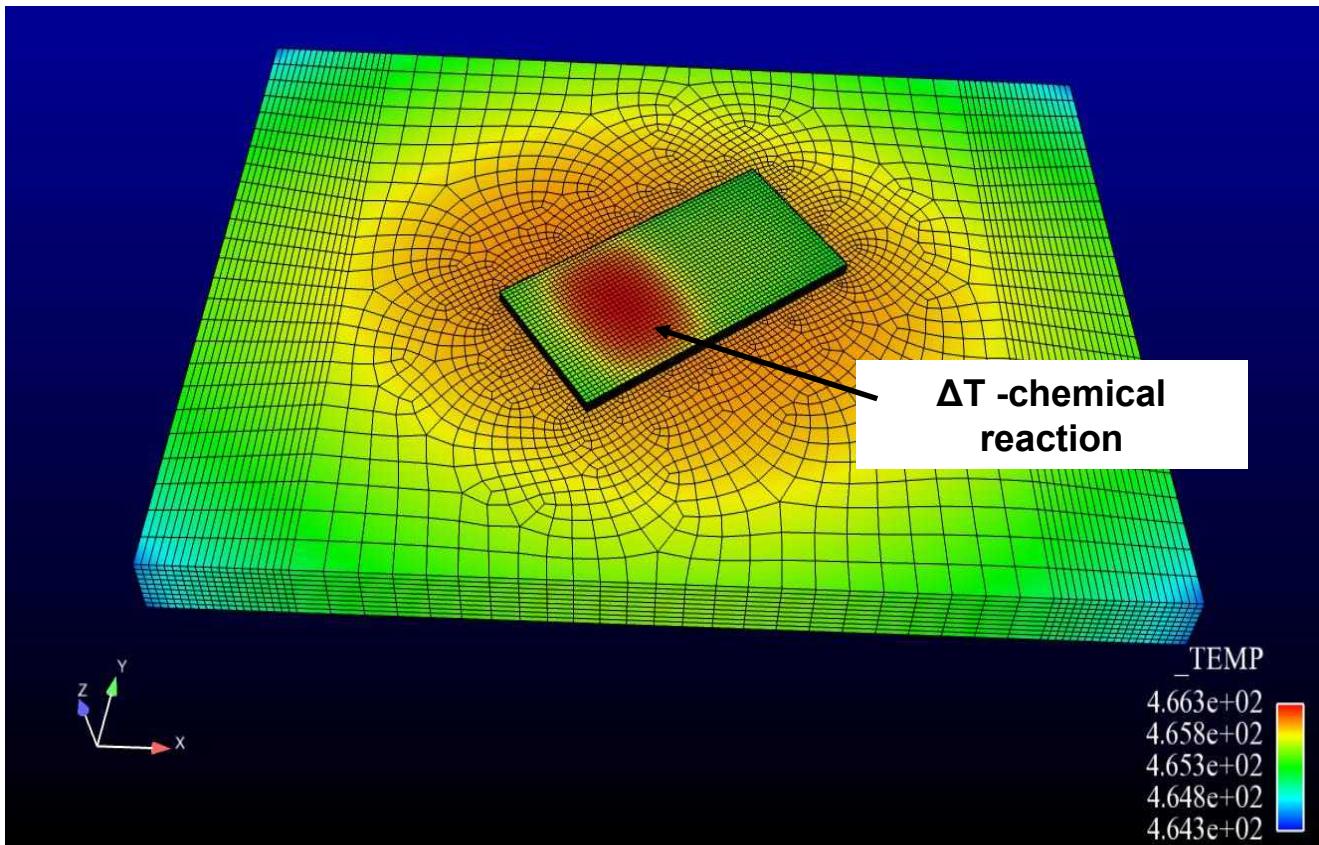


Equivalent thermal circuit

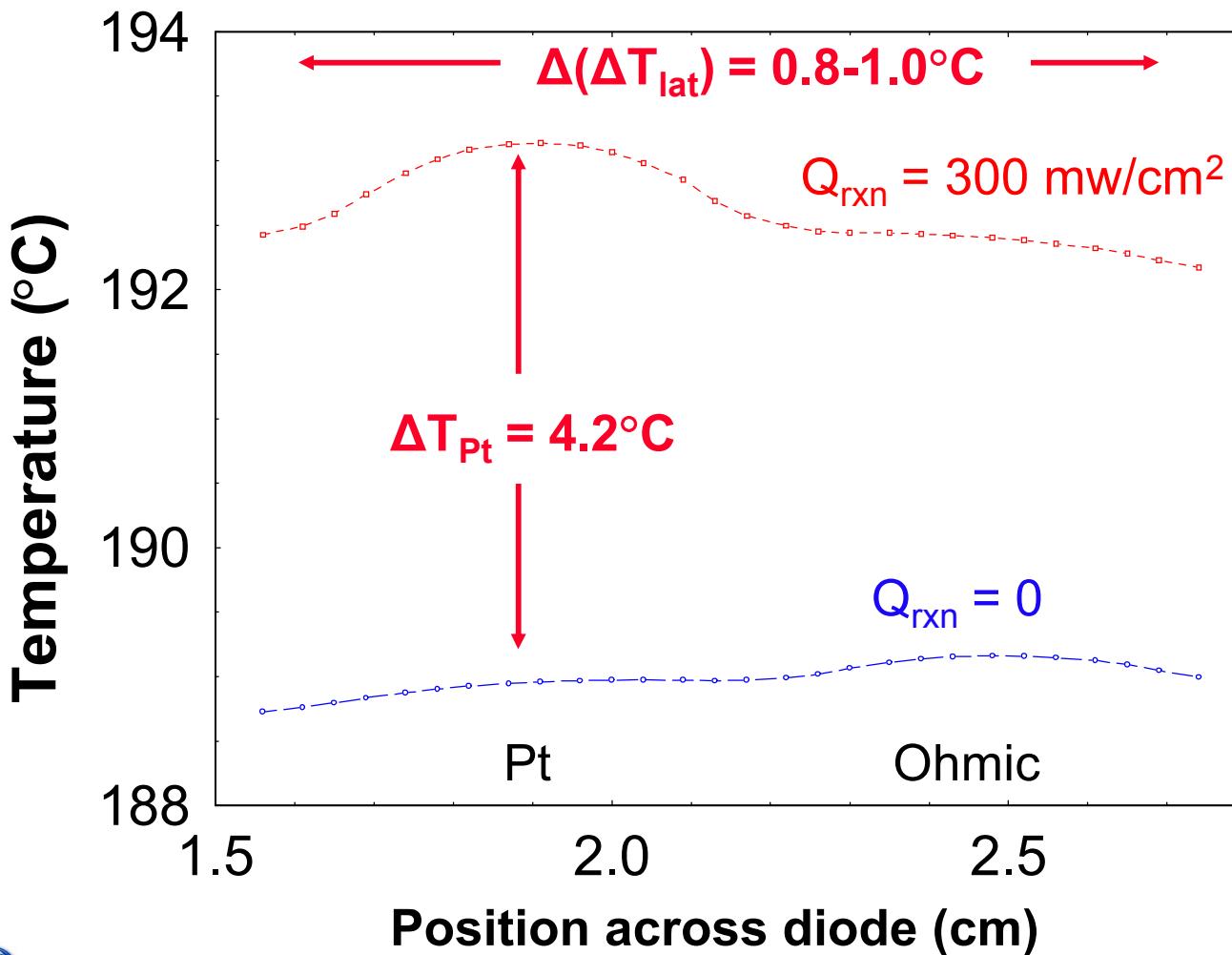




# Full 3D simulation



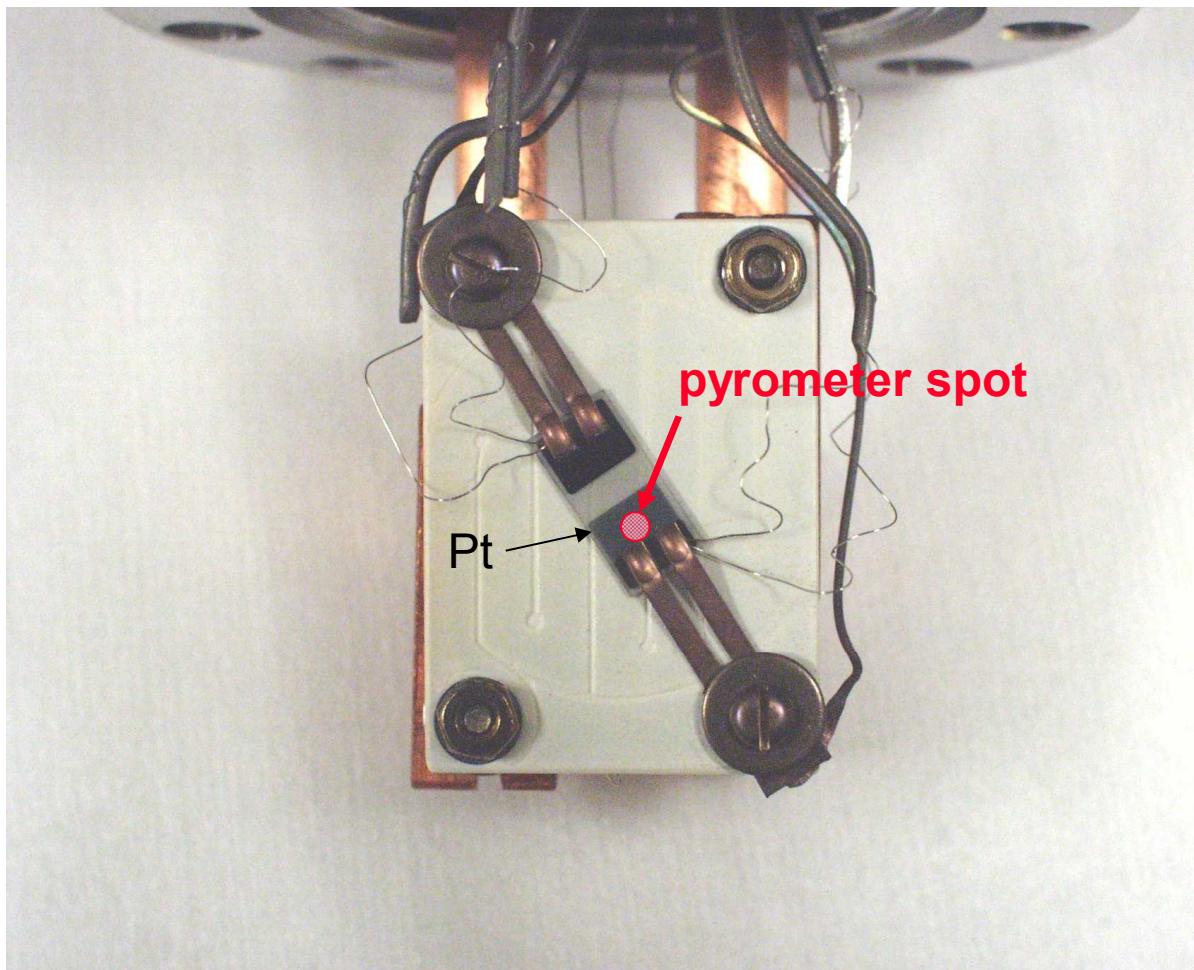
# Full 3D simulation



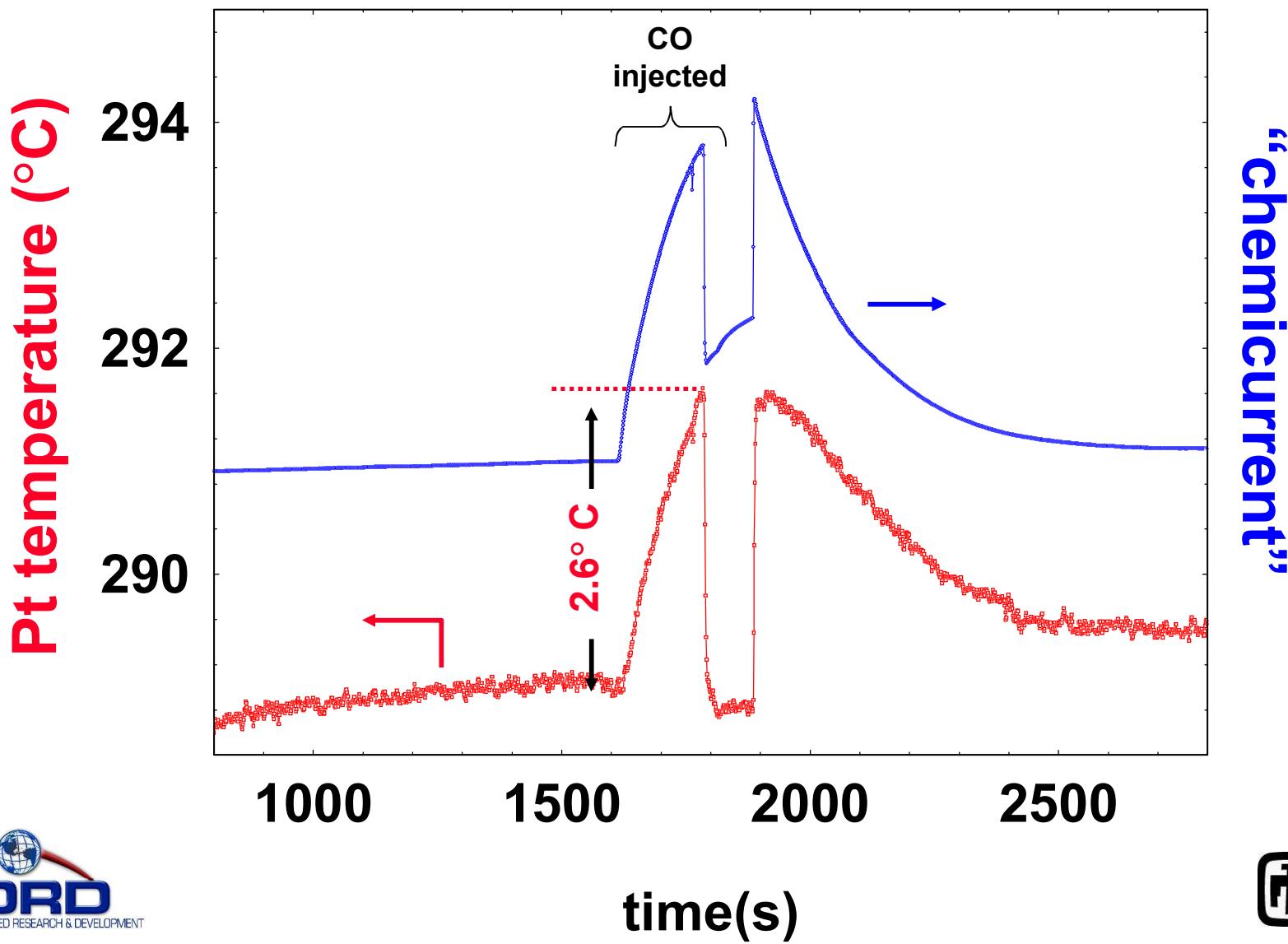


# Experimental methods of temperature measurement

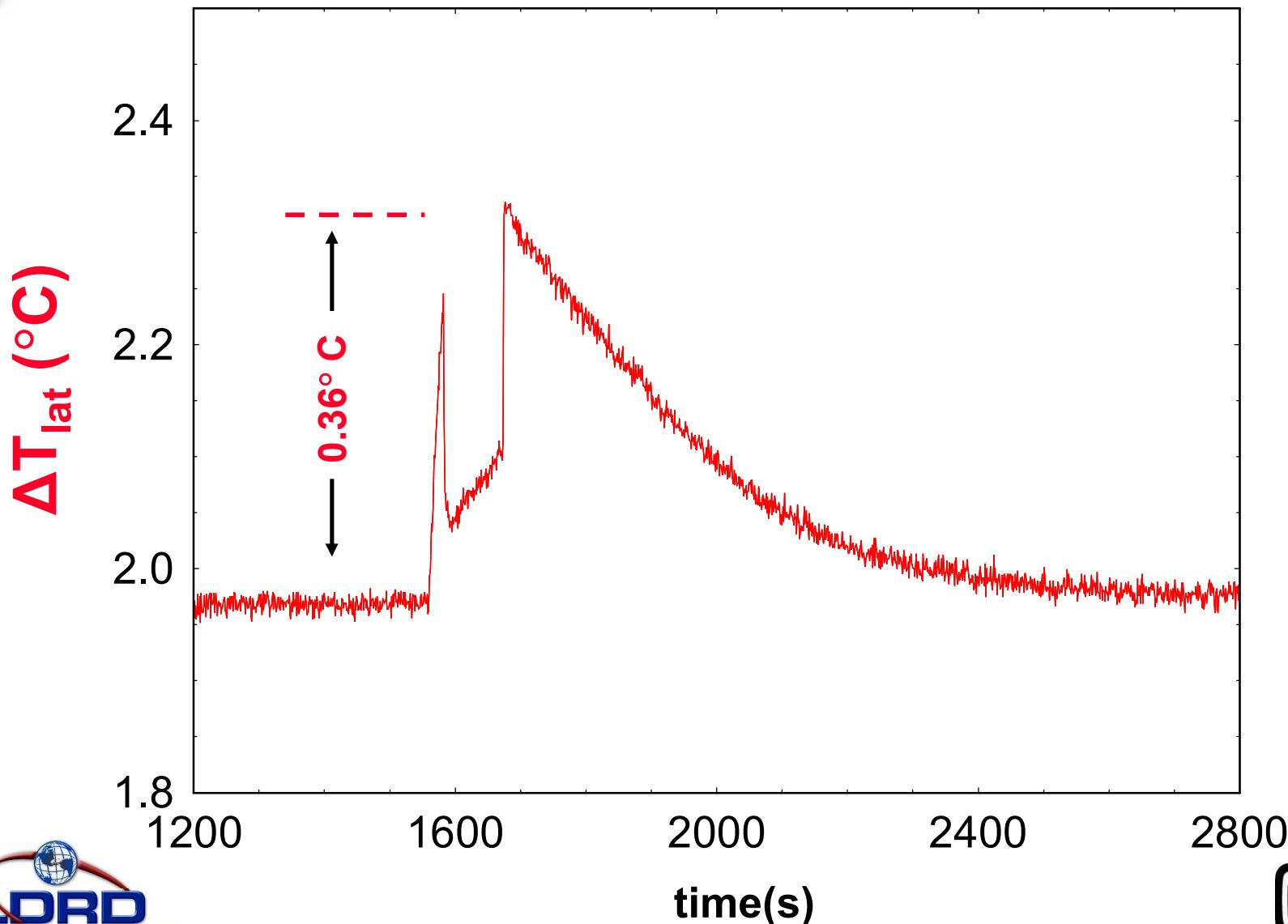
Nanodiode mounted with thermocouples on contacts



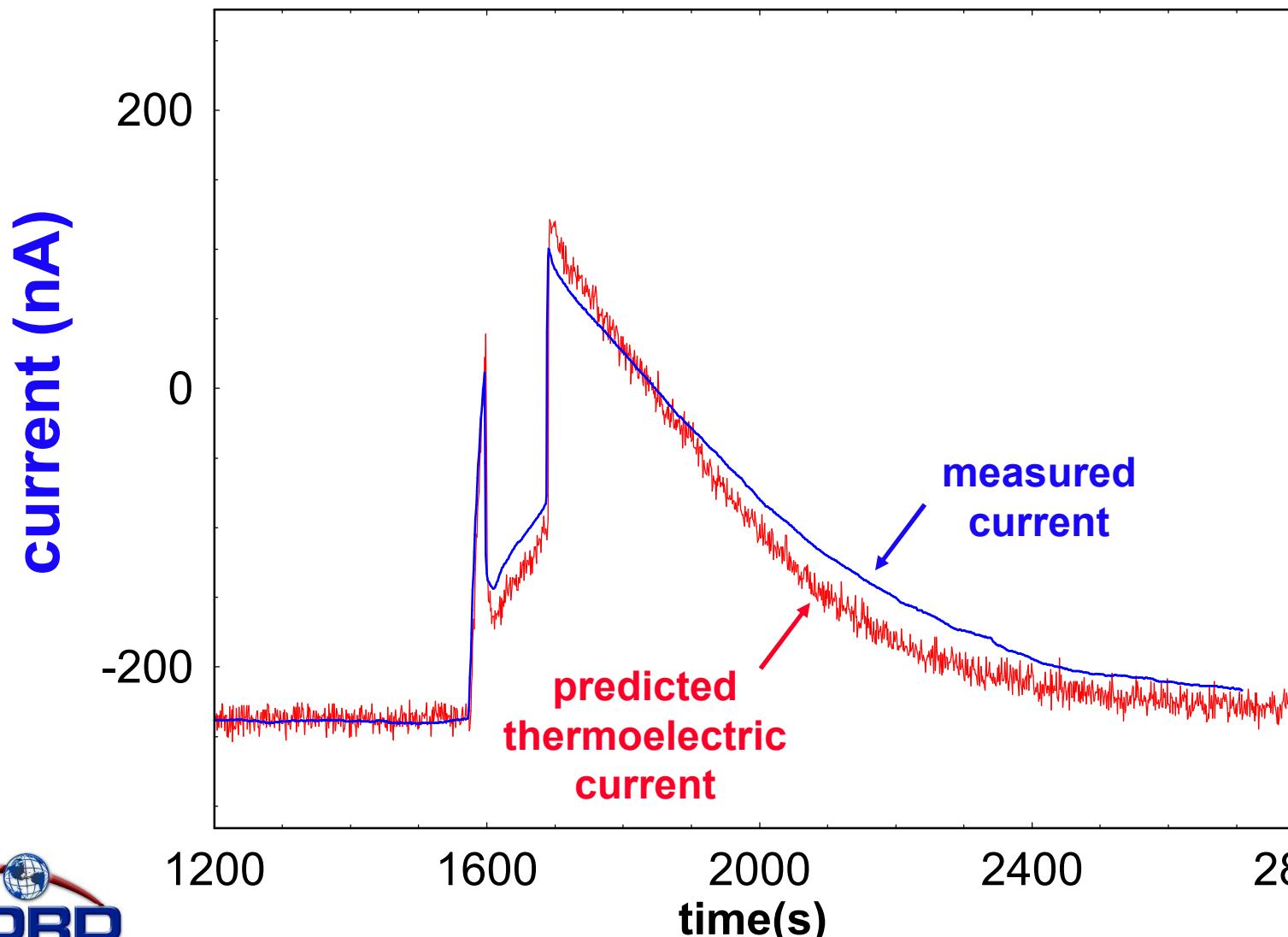
mid-IR (7.5  $\mu\text{m}$ ) pyrometer unambiguously measures  
Pt surface temperature rise during reaction



thermocouples are used to measure the lateral temperature gradient during reaction



Observed current can be quantitatively explained using  $\Delta T_{lat}$ , the Seebeck Coef, and the diode resistance, it is entirely due to thermoelectric voltage





Our calculations and measurements conclusively demonstrate surface temperature rises of a **1-5 °C**, and lateral temperature gradients of **0.2-1.0 °C**

In contrast, Park et al. (Top Cat 2007) concluded that the temperature increase during reaction was negligible (< **10<sup>-3</sup> °C**), and therefore **dismissed the thermoelectric effect**

→ They only considered the vertical temperature gradient within the thin Pt and TiO<sub>2</sub> layers ( $\Delta T_{\perp}$ ), which significantly underestimates the temperature changes from the reaction exothermicity



# Summary

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- We have fabricated Pt/GaN and Pt/TiO<sub>2</sub> nanodiodes that exhibit **unmistakable kinetic signatures** of the CO + O<sub>2</sub> reaction, the electronic signal is derived from the **chemical reaction**
- However, the signal dependence on diode shunt resistance indicates that it is **derived from a voltage source**
- With appropriate temperature calculations & measurements, all attributes of the chemical signal can be qualitatively and quantitatively explained by reaction exothermicity and the **thermoelectric properties** of the diode
- measured current is thermoelectric in origin **it is not true chemicurrent**